

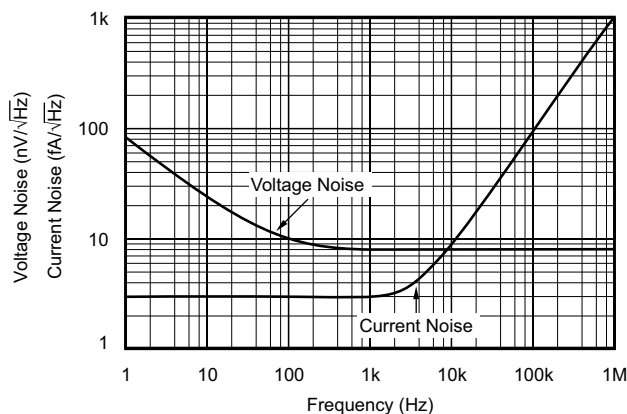
OPAx132 高速 FET 入力オペアンプ

1 特長

- このデバイスには、より新しいバージョンが存在します。
[OPA2156](#)
- FET 入力: $I_B =$ 最大 50pA
- 広い帯域幅: 8MHz
- 高いスルーレート: 20V/ μ s
- 低ノイズ: 8nV/ $\sqrt{\text{Hz}}$ (1kHz)
- 低歪: 0.00008%
- 高いオープンループゲイン: 126dB (2k Ω 負荷)
- 幅広い電源電圧範囲: $\pm 2.5\text{V} \sim \pm 18\text{V}$
- 低いオフセット電圧: 最大 500 μ V
- シングル、デュアル、クワッドの各バージョン

2 アプリケーション

- SAR ADC ドライバ
- 基準電圧バッファ
- トランスインピーダンスアンプ
- フォトダイオードアンプ
- アクティブフィルタ
- 積分器



低ノイズ JFET 入力

3 概要

OPA132、OPA2132、OPA4132 (OPAx132) FET 入力オペアンプシリーズは優れた高速性と DC 性能を特長としています。高いスルーレートと広い帯域幅の組み合わせは、高速なセトリング時間をもたらします。シングル、デュアル、クワッドの各製品で同一の仕様を備え、設計の柔軟性を高めています。シングルおよびデュアルバージョンでは、高性能グレードを利用できます。いずれのデバイスも、汎用、オーディオ、データアキュイジション、通信アプリケーション (特にソースインピーダンスが高い場合) に最適です。

OPAx132 オペアンプは使いやすく、一般的な FET 入力オペアンプでしばしば見られるような位相反転と過負荷の問題を引き起こしません。入力カスコード回路は、優れた同相信号除去を実現し、広い入力電圧範囲にわたって低い入力バイアス電流を維持します。OPAx132 シリーズのオペアンプはユニティゲインにおいて安定であり、大きな負荷容量を含む幅広い負荷条件にわたって優れた動的挙動を示します。デュアルおよびクワッドバージョンは完全に独立した回路を使用しているため、オーバードライブまたは過負荷時でも、クロストークが最小限に抑えられ、相互作用が発生しません。

シングルバージョンは 8 ピン SOIC 表面実装パッケージで供給され、デュアルバージョンは 8 ピン DIP および SOIC 表面実装パッケージで供給されます。クワッドバージョンは SOIC 表面実装パッケージで供給されます。すべてのデバイスは $-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$ で動作が規定されています。

[OPA2156](#) は次世代バージョンであり、小さい広帯域ノイズ (3nV/ $\sqrt{\text{Hz}}$)、広い帯域幅 (25MHz)、レールツーレール入力を特長としています。

製品情報

部品番号	チャンネル数	パッケージ ⁽¹⁾
OPA132	シングル	D (SOIC, 8)
OPA2132	デュアル	D (SOIC, 8)
		P (PDIP, 8)
OPA4132	クワッド	D (SOIC, 14)

(1) 詳細については、[セクション 10](#) を参照してください。



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4 Pin Configuration and Functions

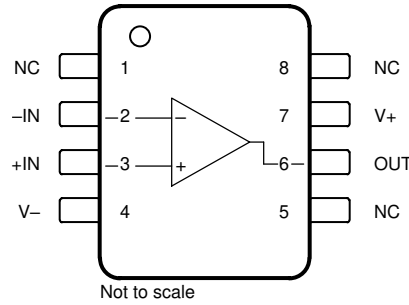


図 4-1. OPA132: D Package, 8-Pin SOIC (Top View)

Pin Functions: OPA132

PIN		TYPE	DESCRIPTION
NAME	NO.		
+IN	3	Input	Noninverting input
-IN	2	Input	Inverting input
NC	1, 5	—	Do not connect these pins ⁽¹⁾
NC	8	—	No internal connection. Float this pin.
Output	6	Output	Output
V+	7	Power	Positive power supply
V-	4	Power	Negative power supply

(1) Existing layouts for the OPA132 before revision C of this data sheet do not need to be redesigned.

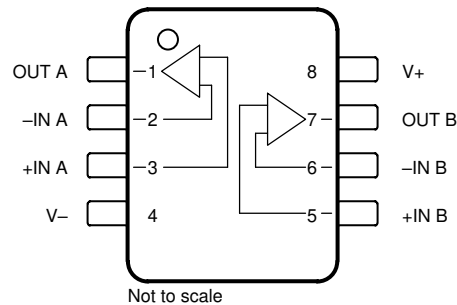


図 4-2. OPA2132: D Package, 8-Pin SOIC, and P Package, 8-Pin PDIP (Top View)

表 4-1. Pin Functions: OPA2132

PIN		TYPE	DESCRIPTION
NAME	NO.		
+IN A	3	Input	Noninverting input, channel A
+IN B	5	Input	Noninverting input, channel B
-IN A	2	Input	Inverting input, channel A
-IN B	6	Input	Inverting input, channel B
OUT A	1	Output	Output, channel A
OUT B	7	Output	Output, channel B
V+	8	Power	Positive (highest) power supply
V-	4	Power	Negative (lowest) power supply

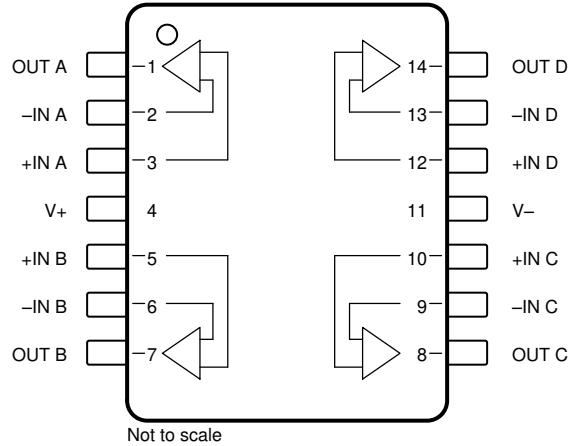


図 4-3. OPA4132- D Package, 14-Pin SOIC (Top View)

表 4-2. Pin Functions: OPA4132

PIN		TYPE	DESCRIPTION
NAME	NO.		
+IN A	3	Input	Noninverting input, channel A
+IN B	5	Input	Noninverting input, channel B
+IN C	10	Input	Noninverting input, channel C
+IN D	12	Input	Noninverting input, channel D
-IN A	2	Input	Inverting input, channel A
-IN B	6	Input	Inverting input, channel B
-IN C	9	Input	Inverting input, channel C
-IN D	13	Input	Inverting input, channel D
OUT A	1	Output	Output, channel A
OUT B	7	Output	Output, channel B
OUT C	8	Output	Output, channel C
OUT D	14	Output	Output, channel D
V+	4	Power	Positive (highest) power supply
V-	11	Power	Negative (lowest) power supply

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _S	Supply voltage, (V+) – (V–)		36	V
	Input voltage ⁽²⁾	(V–) – 0.5	(V+) + 0.5	V
	Input current ⁽²⁾		±10	mA
I _{SC}	Output short-circuit ⁽³⁾	Continuous		
T _A	Operating temperature	–40	125	°C
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	–55	125	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails must be current limited to 10mA or less.
- (3) Short-circuit to ground, one amplifier per package.

5.2 ESD Ratings

			VALUE	UNIT
OPA132 in SOIC Package, OPA2132 in PDIP Package				
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
OPA2132 in SOIC Package				
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	
OPA4132				
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±200	

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _S	Supply voltage, (V+) – (V–)	Dual supply	±2.5	±15	±18	V
		Single supply	9	30	36	
T _A	Ambient temperature		–40		85	°C

5.4 Thermal Information - OPA132

THERMAL METRIC ⁽¹⁾		OPA132		UNIT
		D (SOIC)		
		8 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	160		°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	75		°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	60		°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9		°C/W
Ψ_{JB}	Junction-to-board characterization parameter	50		°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A		°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

5.5 Thermal Information - OPA2132

THERMAL METRIC ⁽¹⁾		OPA2132		UNIT
		D (SOIC)	P (PDIP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	160	71	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	75	50	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	60	36	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9	16	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	50	35	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

5.6 Thermal Information - OPA4132

THERMAL METRIC ⁽¹⁾		OPA4132		UNIT
		D (SOIC)		
		14 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	97		°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	56		°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	53		°C/W
Ψ_{JT}	Junction-to-top characterization parameter	19		°C/W
Ψ_{JB}	Junction-to-board characterization parameter	46		°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A		°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

5.7 Electrical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $R_L = 2\text{k}\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} = \text{midsupply}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	OPAx132U			± 0.2	± 0.5	mV
		OPAx132UA			± 0.5	± 2	
dV_{OS}/dT	Input offset voltage drift	$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			± 2	± 10	$\mu\text{V}/^\circ\text{C}$
PSRR	Power-supply rejection ratio	$\pm 2.5\text{V} \leq V_S \leq \pm 18\text{V}$	OPAx132U		± 5	± 15	$\mu\text{V}/\text{V}$
			OPAx132UA		± 5	± 30	
	Channel separation (dual and quad)	$R_L = 2\text{k}\Omega$			0.2		$\mu\text{V}/\text{V}$
INPUT BIAS CURRENT							
I_B	Input bias current ⁽¹⁾				± 5	± 50	pA
		$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		See Typical Characteristics			
I_{OS}	Input offset current ⁽¹⁾				± 2	± 50	pA
NOISE							
e_n	Input voltage noise density	$f = 10\text{Hz}$			23		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 100\text{Hz}$			10		
		$f = 1\text{kHz}$			8		
		$f = 10\text{kHz}$			8		
I_n	Input current noise density	$f = 1\text{kHz}$			3		$\text{fA}/\sqrt{\text{Hz}}$
INPUT VOLTAGE							
V_{CM}	Common-mode voltage			$(V_-) + 2.5$	± 13	$(V_+) - 3.5$	V
CMRR	Common-mode rejection ratio	$-12.5\text{V} \leq V_{CM} \leq 11.5\text{V}$		OPAx132U	96	100	dB
				OPAx132UA	86	94	
INPUT IMPEDANCE							
	Differential				$10^{13} \parallel 10$		$\Omega \parallel \text{pF}$
	Common-mode	$-12.5\text{V} \leq V_{CM} \leq 11.5\text{V}$			$10^{13} \parallel 7$		
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	$R_L = 10\text{k}\Omega$, $-14.5\text{V} \leq V_O \leq 13.8\text{V}$	OPAx132U	110	120		dB
			OPAx132UA	104	120		
		$R_L = 2\text{k}\Omega$, $-13.8\text{V} \leq V_O \leq 13.5\text{V}$	OPAx132U	110	126		
			OPAx132UA	104	120		
		$R_L = 600\Omega$, $-12.8\text{V} \leq V_O \leq 12.5\text{V}$	OPAx132U	110	130		
			OPAx132UA	104	120		
FREQUENCY RESPONSE							
GBW	Gain bandwidth product				8		MHz
SR	Slew rate				± 20		V/ μs
	Settling time	10V step, $G = 1$, $C_L = 100\text{pF}$	0.1%		0.7		μs
			0.01%		1		
THD+N	Total harmonic distortion plus noise	$f = 1\text{kHz}$, $G = 1$, $V_O = 3.5V_{\text{rms}}$	$R_L = 2\text{k}\Omega$		0.0008%		
			$R_L = 600\Omega$		0.0009%		
	Overload recovery time	$G = \pm 1$			600		ns
OUTPUT							
V_O	Voltage output	$R_L = 10\text{k}\Omega$	Positive	$(V_+) - 1.2$	$(V_+) - 0.9$		V
			Negative		$(V_-) + 0.3$	$(V_-) + 0.5$	
		$R_L = 2\text{k}\Omega$	Positive	$(V_+) - 1.5$	$(V_+) - 1.1$		
			Negative		$(V_-) + 1.2$	$(V_-) + 0.9$	
		$R_L = 600\Omega$	Positive	$(V_+) - 2.5$	$(V_+) - 2.0$		
			Negative		$(V_-) + 2.2$	$(V_-) + 1.5$	
I_{SC}	Short-circuit current	Sourcing		36		mA	
		Sinking		-30		mA	
	Capacitive load drive (stable operation)				See Typical Characteristics		
POWER SUPPLY							

OPA132, OPA2132, OPA4132

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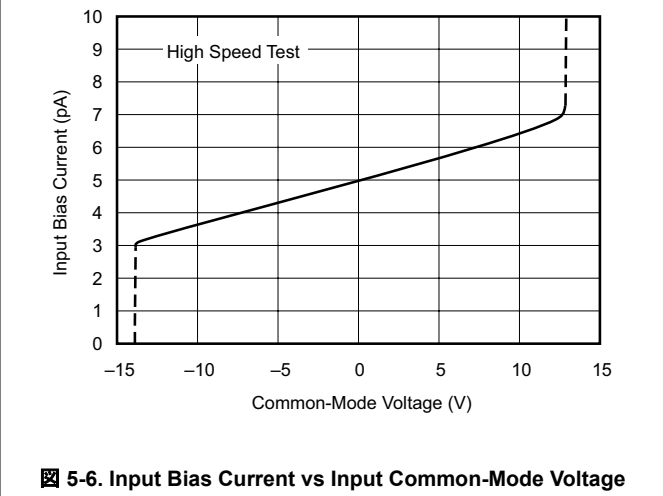
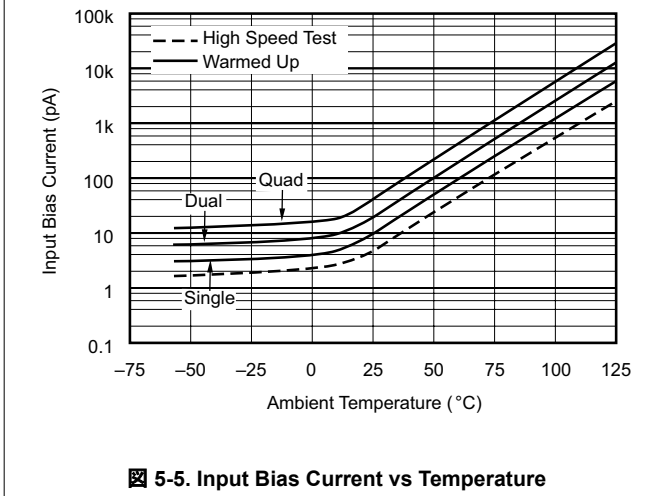
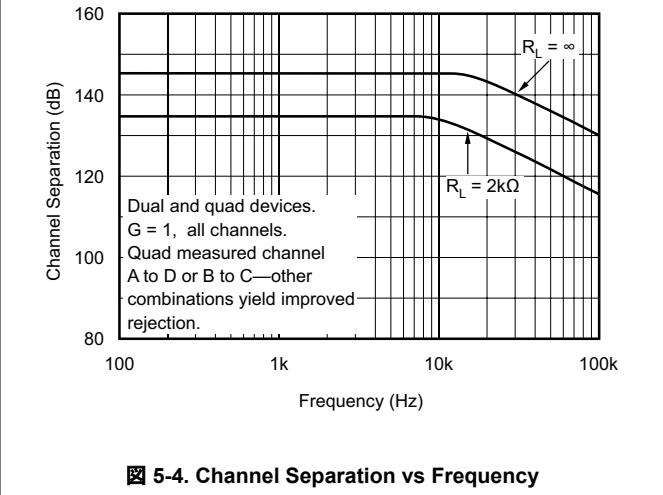
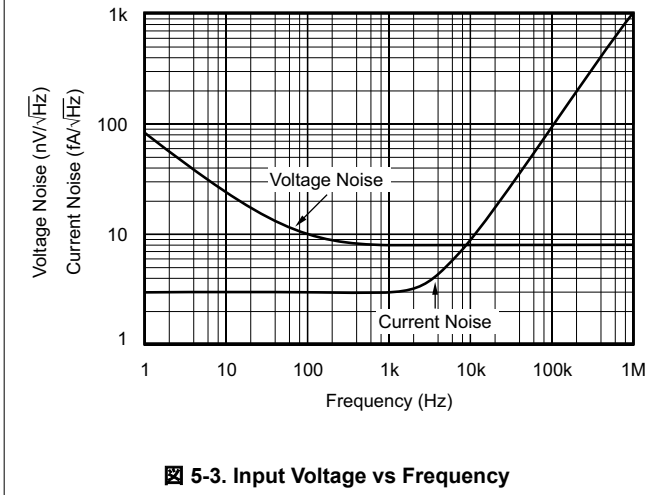
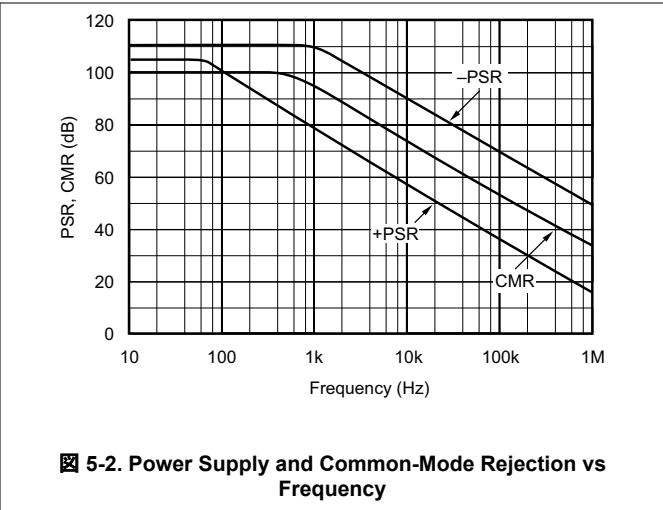
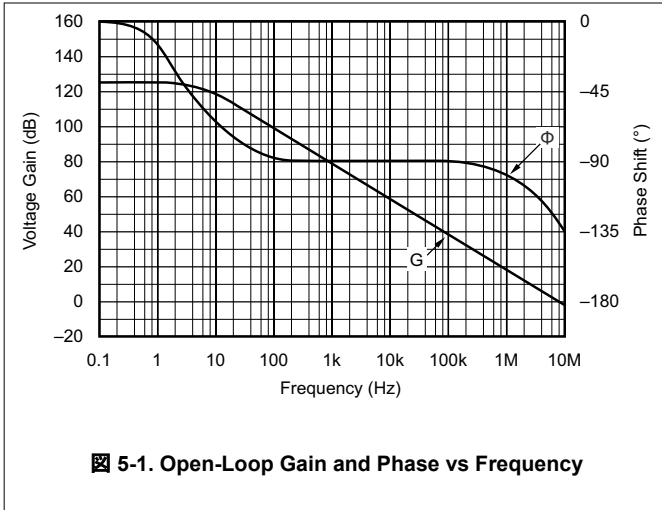
 at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $R_L = 2\text{k}\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} = \text{midsupply}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_Q	Quiescent current (per amplifier)	$I_O = 0\text{mA}$		± 4	± 4.8	mA

 (1) High-speed test at $T_J = 25^\circ\text{C}$.

5.8 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $R_L = 2\text{k}\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} = \text{midsupply}$ (unless otherwise noted)



5.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $R_L = 2\text{k}\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} = \text{midsupply}$ (unless otherwise noted)

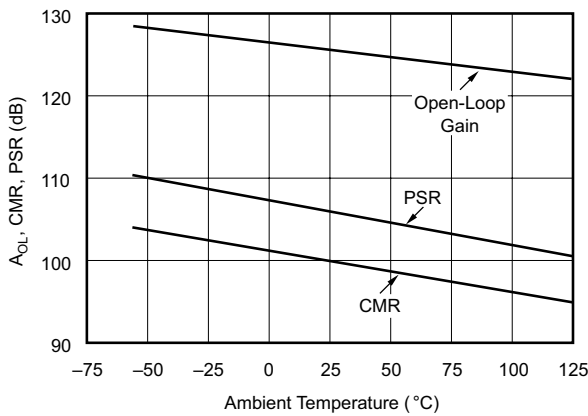


Fig 5-7. A_{OL} , CMR, PSR vs Temperature

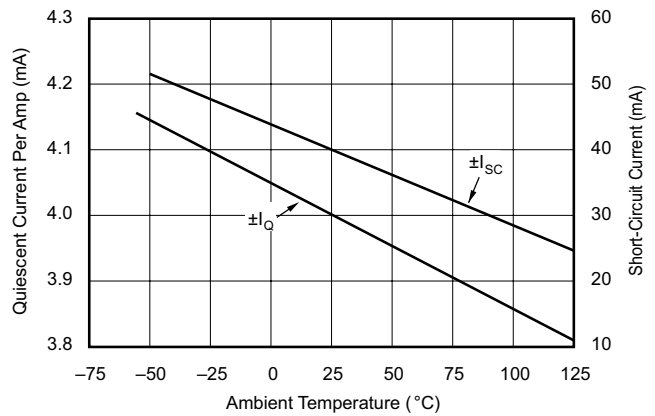


Fig 5-8. Quiescent Current and Short-Circuit Current vs Temperature

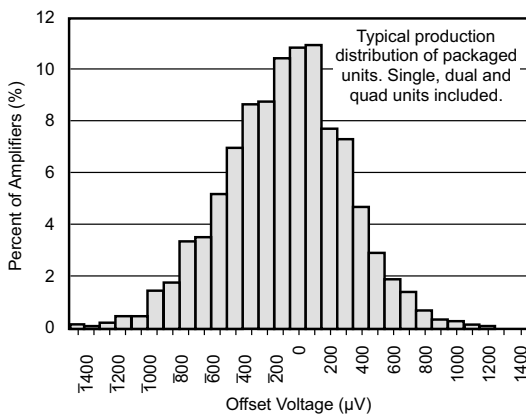


Fig 5-9. Offset Voltage Production Distribution

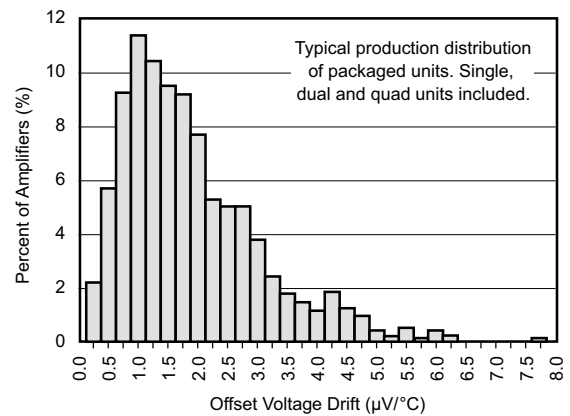


Fig 5-10. Offset Voltage Drift Production Distribution

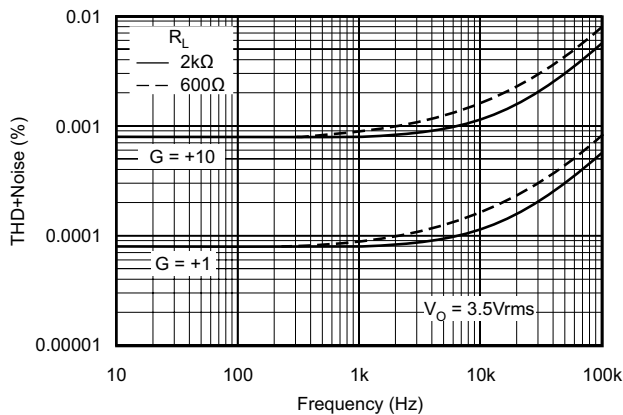


Fig 5-11. Total Harmonic Distortion + Noise vs Frequency

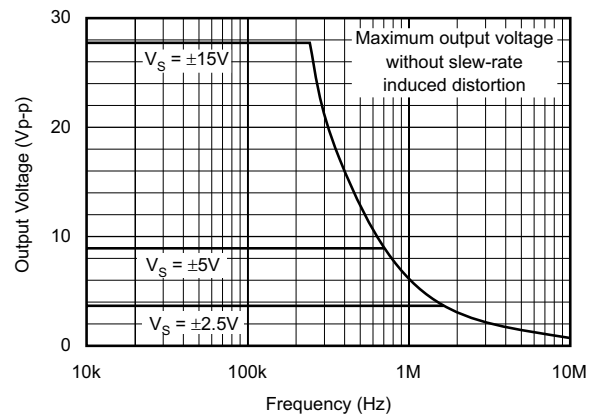
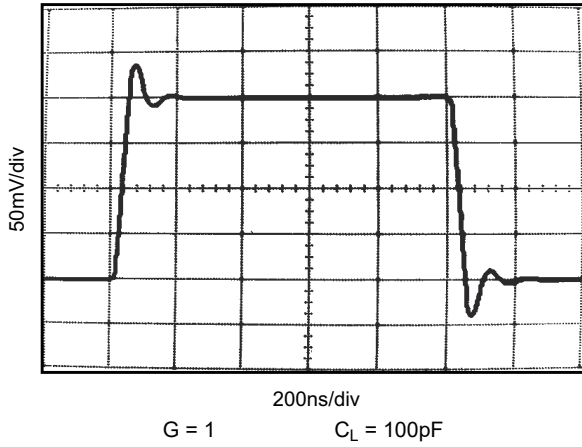


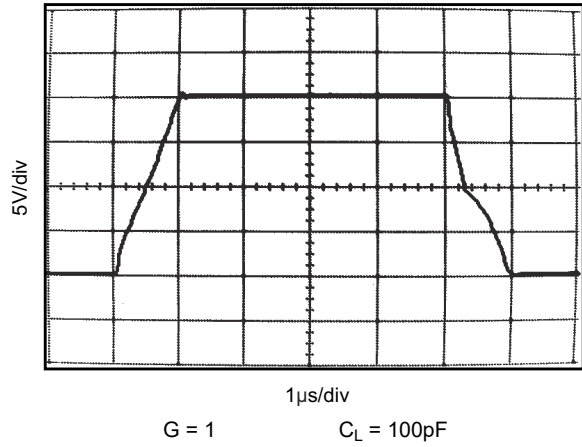
Fig 5-12. Maximum Output Voltage vs Frequency

5.8 Typical Characteristics (continued)

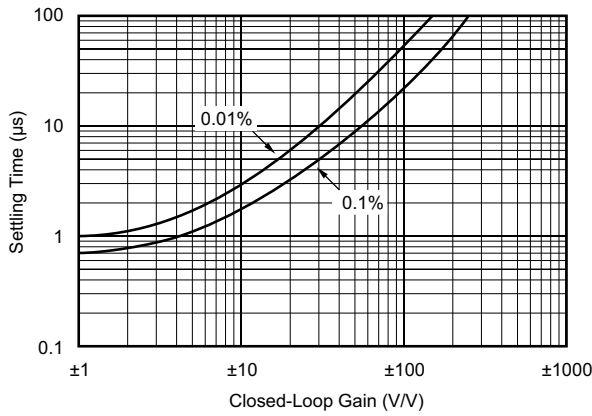
at $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $R_L = 2\text{k}\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} = \text{midsupply}$ (unless otherwise noted)



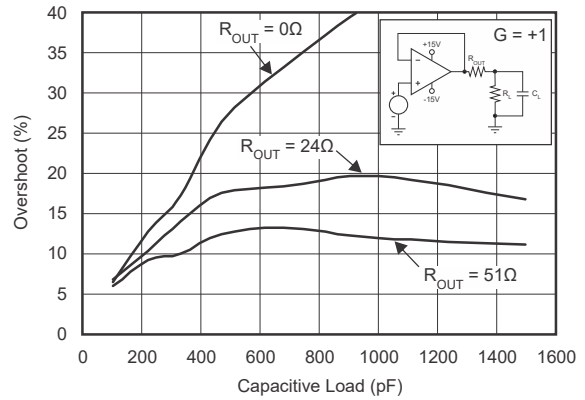
5-13. Small-Signal Step Response



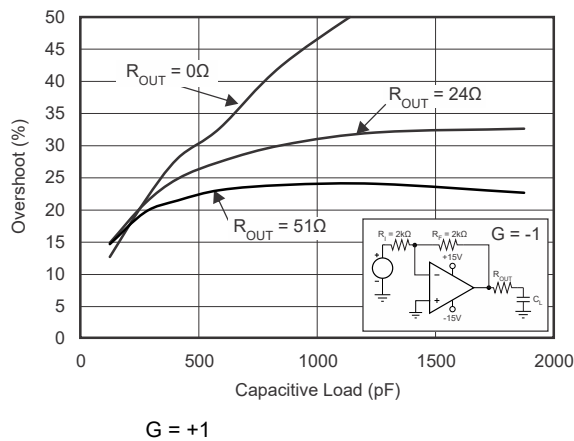
5-14. Large-Signal Step Response



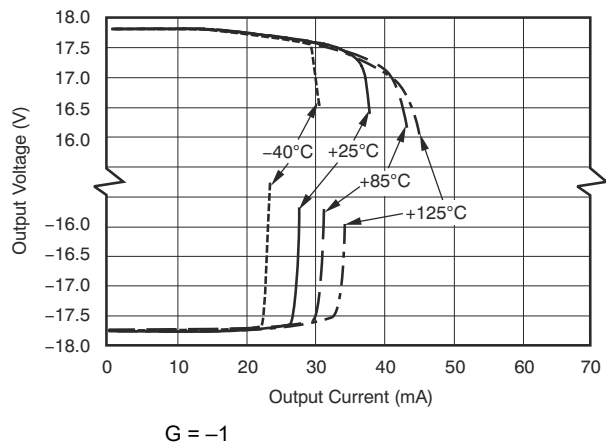
5-15. Settling Time vs Closed-Loop Gain



5-16. Small-Signal Overshoot vs Load Capacitance



5-17. Small-Signal Overshoot vs Load Capacitance



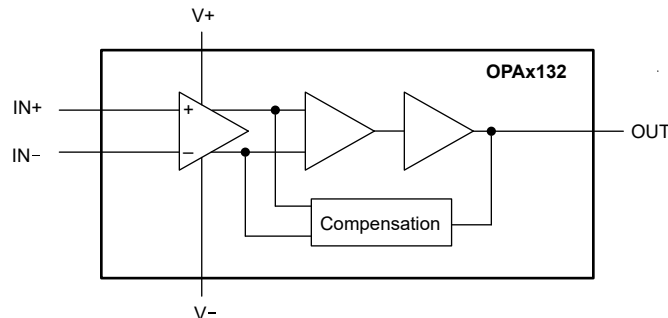
5-18. Output Voltage Swing vs Output Current

6 Detailed Description

6.1 Overview

The OPAx132 series of FET-input operational amplifiers provides high speed and excellent dc performance. The combination of high slew rate and wide bandwidth provide fast settling time. Single, dual, and quad versions have identical specifications for maximum design flexibility. High performance grades are available in the single and dual versions. All devices are an excellent choice for general-purpose, audio, data acquisition and communications applications; especially, where high source impedance is encountered.

6.2 Functional Block Diagram



6.3 Feature Description

The OPAx132 series of JFET operational amplifiers combine low noise and wide bandwidth with precision and low input bias current to make these devices an excellent choice for applications with a high source impedance. The OPAx132 is unity-gain stable and features high slew rate ($\pm 20\text{V}/\mu\text{s}$) and wide bandwidth (8MHz).

6.4 Device Functional Modes

The OPAx132 has a single functional mode and is operational when the power-supply voltage is greater than 5V ($\pm 2.5\text{V}$). The maximum power supply voltage for the OPAx132 is 36V ($\pm 18\text{V}$).

7 Application and Implementation

注

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7.1 Application Information

The OPAX132 series operational amplifiers are unity-gain stable and an excellent choice for a wide range of general-purpose applications. Bypass power-supply pins with 10nF ceramic capacitors or larger.

The OPAX132 series operational amplifiers are free from unexpected output phase reversal common with FET operational amplifiers. Many FET-input operational amplifiers exhibit phase-reversal of the output when the input common-mode voltage range is exceeded. This phase reversal can occur in voltage-follower circuits, causing serious problems in control-loop applications. The OPAX132 series of operational amplifiers are free from this undesirable behavior. All circuitry is completely independent in dual and quad versions, maintaining normal behavior when one amplifier in a package is overdriven or short-circuited.

7.1.1 Operating Voltage

The OPAX132 series of operation amplifiers operate with power supplies from $\pm 2.5\text{V}$ to $\pm 18\text{V}$ with excellent performance. Although specifications are production tested with $\pm 15\text{V}$ supplies, most behavior remains unchanged throughout the full operating voltage range. Parameters which vary significantly with operating voltage are shown in [セクション 5.8](#).

7.1.2 Offset Voltage Trim

The offset voltage of the OPAX132 amplifiers is laser trimmed and usually requires no user adjustment. The OPAX132 provide less than $\pm 500\mu\text{V}$ of input offset voltage and less than $10\mu\text{V}/^\circ\text{C}$ of input offset voltage drift over the operating temperature range

7.1.3 Input Bias Current

The FET-inputs of the OPAX132 series provide very low input bias current and cause negligible errors in most applications. For applications where low input bias current is crucial, minimize junction temperature rise. The input bias current of FET-input operational amplifiers increases with temperature; see also [図 5-5](#).

The OPAX132 series can be operated at reduced power supply voltage to minimize power dissipation and temperature rise. Using $\pm 3\text{V}$ supplies reduces power dissipation to one-fifth used at $\pm 15\text{V}$.

The dual and quad versions have higher total power dissipation than the single version, leading to higher junction temperature. Thus, a warmed-up quad has higher input bias current than a warmed-up single. Furthermore, an SOIC generally has higher junction temperature than a DIP at the same ambient temperature because of a larger θ_{JA} .

Printed-circuit-board (PCB) layout also helps minimize junction temperature rise. Minimize temperature rise by soldering the devices to the PCB rather than using a socket. Wide copper traces also help dissipate the heat by acting as an additional heat sink.

Input stage cascode circuitry keeps the input bias current virtually unchanged throughout the full input common-mode range of the OPAX132 series. See also [図 5-6](#).

7.2 Typical Application

The OPAx132 family offers outstanding dc precision and ac performance. These devices operate up to 36V supply rails and offer ultra-low input bias current and input bias current noise, as well as 8MHz bandwidth and high capacitive load drive. These features make the OPAx132 a robust, high-performance operational amplifier for high-voltage industrial applications with high source impedance.

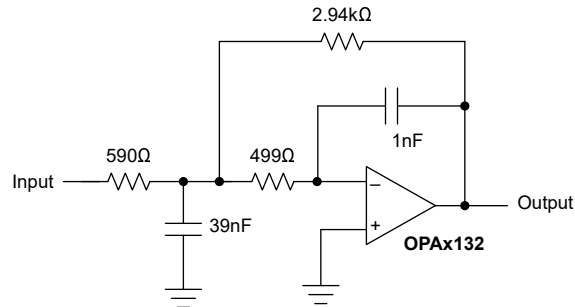


图 7-1. OPA132 2nd Order 30kHz, Low Pass Filter Schematic

7.2.1 Design Requirements

Use the following parameters for this application:

- Gain = 5V/V
- Low-pass cutoff frequency = 30kHz
- -40dB/dec filter response
- Maintain less than 3dB gain peaking in the gain versus frequency response

7.2.2 Detailed Design Procedure

WEBENCH® Circuit Designer creates customized power supply and active filter circuits based on your system requirements. The environment gives you end-to-end selection, design, and simulation capabilities that save you time during all phases of the analog design process.

Use our tools to help with your designs:

- [Filter design tool](#)
- [Powerstage designer](#)
- [WEBENCH® Power designer](#)
- [PCB thermal calculator](#)

7.2.3 Application Curve

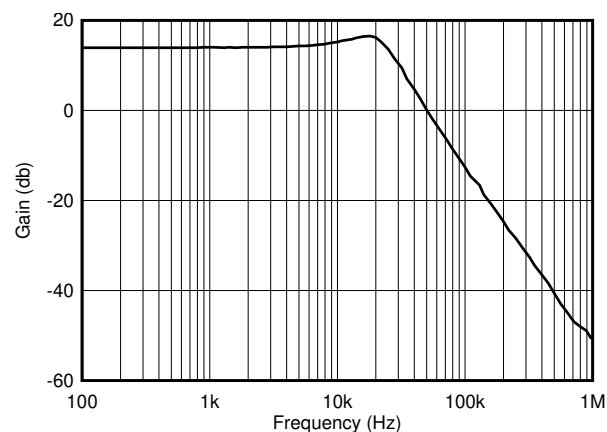


图 7-2. OPA132 2nd-Order 30kHz, Low-Pass Filter Response

7.3 Power Supply Recommendations

The OPAx132 is specified for operation from 5V to 36V ($\pm 2.5V$ to $\pm 18V$); many specifications apply from -40°C to $+85^{\circ}\text{C}$. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in [セクション 5.8](#).

注意

Supply voltages larger than 36V can permanently damage the device; see [セクション 5.1](#).

Place 10nF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see [セクション 7.4.1](#).

7.4 Layout

7.4.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the operational amplifier individually. Use bypass capacitors to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 10nF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds paying attention to the flow of the ground current. For more detailed information, see also [Circuit Board Layout Techniques](#).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep RF and RG close to the inverting input minimizes parasitic capacitance; see also [セクション 7.4.2](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Clean the PCB following board assembly for best performance.
- Any precision integrated circuit can experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, bake the PCB assembly to remove moisture introduced into the device packaging during the cleaning process. A low temperature, post cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

7.4.2 Layout Example

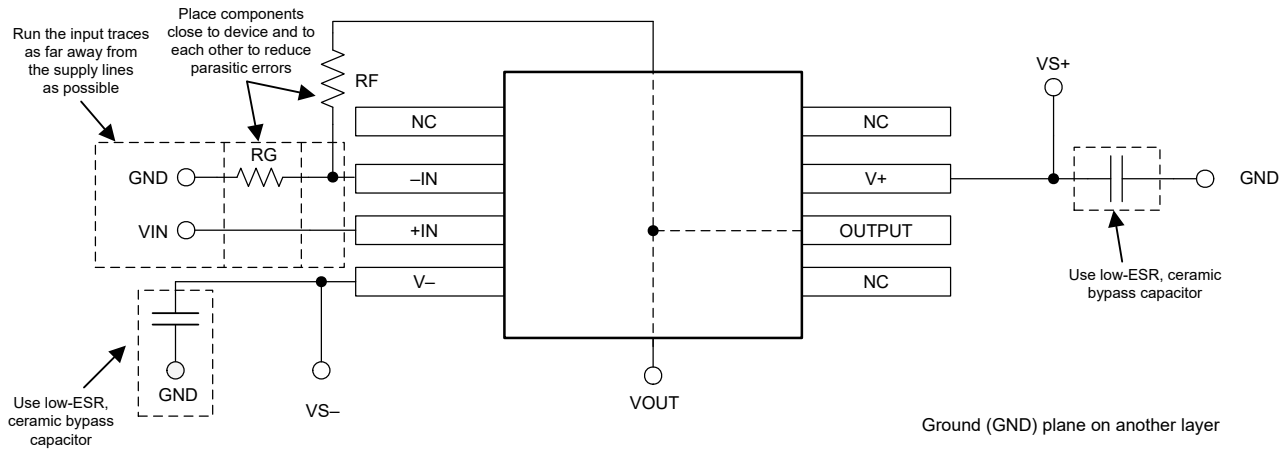
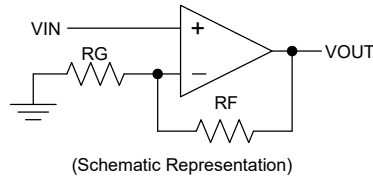


图 7-3. OPA132 Layout Example for the Noninverting Configuration

8 Device and Documentation Support

8.1 Device Support

8.1.1 Development Support

8.1.1.1 Analog Filter Designer

Available as a web-based tool from the [Design and simulation tool](#) web page, the [Analog Filter Designer](#) allows the user to design, optimize, and simulate complete multistage active filter solutions within minutes.

8.1.1.2 TINA-TI™シミュレーション・ソフトウェア (無償ダウンロード)

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8.2 Documentation Support

8.2.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [EMI Rejection Ratio of Operational Amplifiers](#)
- Texas Instruments, [Circuit Board Layout Techniques](#)

8.3 ドキュメントの更新通知を受け取る方法

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8.7 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

9 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision B (September 2015) to Revision C (August 2024)	Page
ドキュメント全体にわたって表、図、相互参照の採番方法を更新.....	1
新しい次世代 OPA2156 に関する情報を追加.....	1
「高いオープン ループ ゲイン」を 130dB (600Ω 負荷) から 126dB (2kΩ 負荷) に変更.....	1
すべてのシングルおよびクワッド チャンネル PDIP パッケージへの言及をこのデータシートから削除.....	1
「製品情報」表を更新.....	1
Updated <i>Pin Configuration and Functions</i> format.....	3
Changed OPA132 pin 1 and pin 8 from "Offset Trim" to "NC".....	3
Changed input voltage from (V-) – 0.7 and (V+) + 0.7 to (V-) – 0.5 and (V+) + 0.5 in <i>Absolute Maximum Ratings</i>	5
Added input current and related footnote to <i>Absolute Maximum Ratings</i>	5
Added <i>Thermal Information</i>	6
Changed format of <i>Electrical Characteristics</i> to latest standard.....	7
Updated nominal conditions in the header of <i>Electrical Characteristics</i>	7
Added ± to power supply rejection ratio (offset vs temperature) and input bias current values.....	7
Changed common-mode voltage MAX value from (V+) – 2.5V to (V+) – 3.5V.....	7
Changed common-mode rejection ratio and common-mode input impedance test conditions from $-12.5V \leq V_{CM} \leq 12.5V$ to $-12.5V \leq V_{CM} \leq 11.5V$	7
Changed differential input impedance from $10^{10}\Omega \parallel 2pF$ to $10^{10}\Omega \parallel 10pF$	7
Changed common-mode input impedance from $10^{10}\Omega \parallel 6pF$ to $10^{10}\Omega \parallel 7pF$	7
Changed overload recovery time from 0.5μs to 600ns.....	7
Changed overload recovery time test condition from $G = \pm$ to $G = \pm 1$ to fix typo.....	7
Moved voltage output negative MIN values to MAX values.....	7
Deleted redundant power supply and temperature range sections already covered in <i>Recommended Operating Conditions</i>	7
Deleted note 1 from <i>Electrical Characteristics</i>	7
Changed <i>Typical Characteristics</i> header test conditions to match <i>Electrical Characteristics</i>	9
Changed Figure 16, <i>Small-Signal Overshoot vs Load Capacitance</i> into two plots, Figure 5-16 for $G = +1$ and Figure 5-17 for $G = -1$	9
Updated Figure 5-18, <i>Output Voltage Swing vs Output Current</i>	9
Updated <i>Functional Block Diagram</i>	12
Updated <i>Offset Voltage Trim</i>	13
Updated Figure 7-3, <i>OPA132 Layout Example for the Noninverting Configuration</i>	16

Changes from Revision A (June 2004) to Revision B (September 2015)

Page

- 「ESD 定格」、「機能説明」、「デバイスの機能モード」、「アプリケーションと実装」、「電源に関する推奨事項」、「レイアウト」、「デバイスおよびドキュメントのサポート」、「メカニカル、パッケージ、および注文情報」の各セクションを追加..... **1**
-

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
OPA132U	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR		OPA 132U	Samples
OPA132U/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR		OPA 132U	Samples
OPA132UA	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	OPA 132U A	Samples
OPA132UA/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	OPA 132U A	Samples
OPA2132P	ACTIVE	PDIP	P	8	50	RoHS & Green	Call TI	N / A for Pkg Type		OPA2132P	Samples
OPA2132PA	ACTIVE	PDIP	P	8	50	RoHS & Green	Call TI	N / A for Pkg Type		OPA2132P A	Samples
OPA2132PAG4	ACTIVE	PDIP	P	8	50	RoHS & Green	Call TI	N / A for Pkg Type		OPA2132P A	Samples
OPA2132U	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	(O2132U, OPA) 2132U	Samples
OPA2132U/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	(O2132U, OPA) 2132U	Samples
OPA2132UA	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	(O2132UA, OPA) 2132U A	Samples
OPA2132UA/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	(O2132UA, OPA) 2132U A	Samples
OPA4132UA	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU NIPDAU-DCC	Level-3-260C-168 HR	-40 to 85	OPA4132UA	Samples
OPA4132UA/2K5	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU NIPDAU-DCC	Level-3-260C-168 HR	-40 to 85	OPA4132UA	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

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PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

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(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA132UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA132UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2132UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2132UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA4132UA/2K5	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
OPA4132UA/2K5	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA132U/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA132U/2K5	SOIC	D	8	2500	353.0	353.0	32.0
OPA132UA/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA132UA/2K5	SOIC	D	8	2500	353.0	353.0	32.0
OPA2132U/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA2132U/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA2132UA/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA2132UA/2K5	SOIC	D	8	2500	353.0	353.0	32.0
OPA4132UA/2K5	SOIC	D	14	2500	353.0	353.0	32.0
OPA4132UA/2K5	SOIC	D	14	2500	356.0	356.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
OPA132U	D	SOIC	8	75	506.6	8	3940	4.32
OPA132UA	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132P	P	PDIP	8	50	506	13.97	11230	4.32
OPA2132PA	P	PDIP	8	50	506	13.97	11230	4.32
OPA2132PAG4	P	PDIP	8	50	506	13.97	11230	4.32
OPA2132U	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132UA	D	SOIC	8	75	506.6	8	3940	4.32
OPA4132UA	D	SOIC	14	50	506.6	8	3940	4.32



D0014A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

EXAMPLE BOARD LAYOUT

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

- Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- This dimension does not include interlead flash.
- Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
 EXPOSED METAL SHOWN
 SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Falls within JEDEC MS-001 variation BA.

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